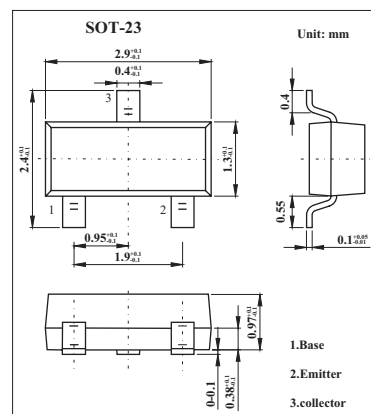


## PNP Silicon Transistor

## 2SC5344SF

## ■ Features

- High hFE.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	35	V
Collector-emitter voltage	V <sub>CE0</sub>	30	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>c</sub>	800	mA
Collector dissipation	P <sub>c</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV <sub>CB0</sub>	I <sub>c</sub> =100μA, I <sub>E</sub> =0	35			V
Collector-emitter breakdown voltage	BV <sub>CE0</sub>	I <sub>c</sub> =1mA, I <sub>B</sub> =0	30			V
Emitter-base breakdown voltage	BV <sub>EB0</sub>	I <sub>E</sub> =10μA, I <sub>c</sub> =0	5			V
Collector cutoff current	I <sub>cBO</sub>	V <sub>CB</sub> =35V, I <sub>E</sub> =0			0.1	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>c</sub> =0			0.1	μA
DC current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> =1V, I <sub>c</sub> =100mA	100		320	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =500mA, I <sub>B</sub> =50mA			0.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>c</sub> =10mA,		120		MHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		19		pF

## ■ hFE Classification

Marking	FA	
	O	Y
hFE	100~200	160~320